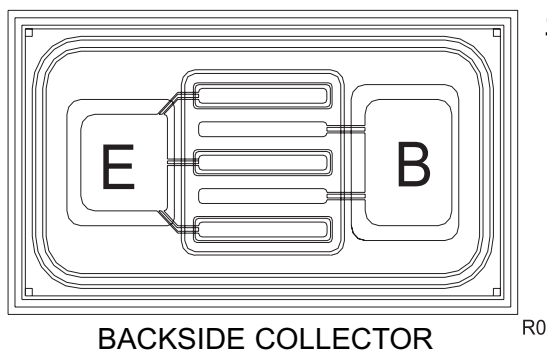


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	12 x 20 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	3.6 X 3.6 MILS
Emitter Bonding Pad Area	3.6 X 3.6 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

**GEOMETRY**



**GROSS DIER PER 4 INCH WAFER**

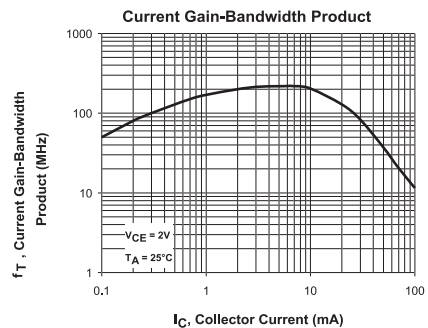
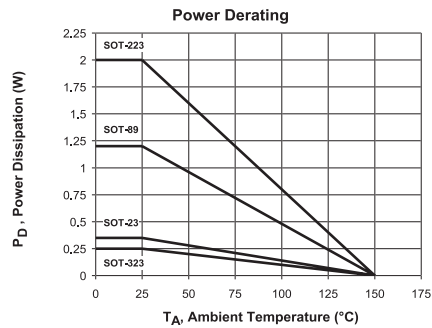
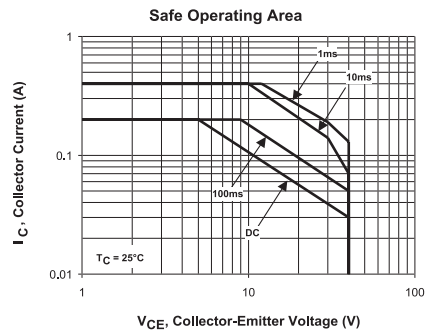
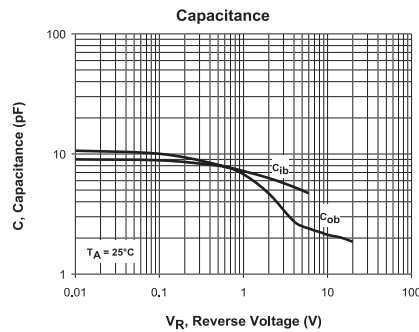
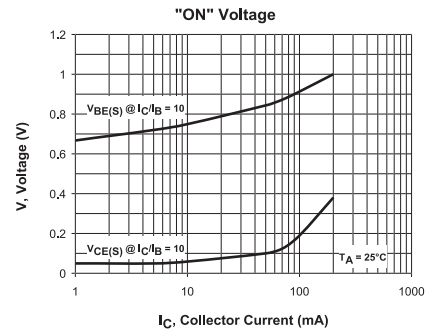
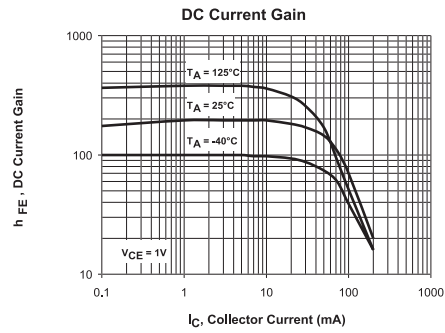
47,150

**PRINCIPAL DEVICE TYPES**

2N3906  
CMKT3906  
CMLT3906E  
CMPT3906  
CMST3906  
CXT3906  
CZT3906

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
[www.centralsemi.com](http://www.centralsemi.com)

R0 (13- February 2006)



145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
[www.centalsemi.com](http://www.centalsemi.com)

R0 (13- February 2006)